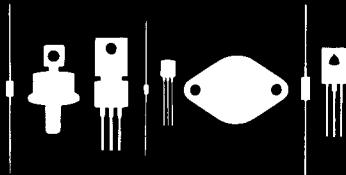


CENTRAL
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Central Semiconductor Corp.
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145 Adams Avenue
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MJE710 MJE711 MJE712 PNP
 MJE720 MJE721 MJE722 NPN
 COMPLEMENTARY SILICON
 PLASTIC POWER TRANSISTORS
 JEDEC TO-126 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MJE710, MJE720 series types are Complementary Silicon Power Transistors designed for low power amplifier and medium speed switching applications.

MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	MJE710 MJE720	MJE711 MJE721	MJE712 MJE722	UNIT
Collector-Base Voltage	V_{CBO}	40	60	80	V
Collector-Emitter Voltage	V_{CEO}	40	60	80	V
Emitter-Base Voltage	V_{EBO}	40	60	80	V
Collect Current	I_C		1.5		A
Base Current	I_B		0.5		A
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D		1.5		W
Power Dissipation	P_D		25		W
Operating and Storage					
Junction Temperature	T_J, T_{STG}		-65 TO +150		$^\circ\text{C}$
Thermal Resistance	θ_{JA}		83.3		$^\circ\text{C}/\text{W}$
Thermal Resistance	θ_{JC}		5.0		$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{CEV}	$V_{CE}=$ Rated $V_{CEO}, V_{BE(OFF)}=1.5\text{V}$		100	μA
$ I_{CEV} $	$V_{CE}=$ Rated $V_{CEO}, V_{BE(OFF)}=1.5\text{V}, T_C=125^\circ\text{C}$		500	μA
$ I_{CEO} $	$V_{CE}=\frac{1}{2}$ Rated V_{CEO}		500	μA
I_{EBO}	$V_{BE}=5.0\text{V}$		1.0	mA
BV_{CEO}	$I_C=50\text{mA}$ (MJE710, MJE720)	40		V
BV_{CEO}	$I_C=50\text{mA}$ (MJE711, MJE721)	60		V
BV_{CEO}	$I_C=50\text{mA}$ (MJE712, MJE722)	80		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.15	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.4	V
$V_{CE(SAT)}$	$I_C=1.5\text{A}, I_B=300\text{mA}$		1.0	V
$V_{BE(SAT)}$	$I_C=1.5\text{A}, I_B=300\text{mA}$		1.3	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$		0.95	V
hFE	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	40		
hFE	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	20		
hFE	$V_{CE}=1.0\text{V}, k=1.0\text{A}$	8.0		